VS-16TTS08-M3, VS-16TTS12-M3

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Thyristor High Voltage, Phase Control SCR, 16 A



-10	-220	JAB	3L

PRIMARY CHARACTERISTICS			
I _{T(AV)}	10 A		
V _{DRM} /V _{RRM}	800 V, 1200 V		
V _{TM}	1.4 V		
I _{GT}	60 mA		
TJ	-40 °C to 125 °C		
Package	TO-220AB 3L		
Circuit configuration	Single SCR		

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55 \text{ °C}, T_J = 125 \text{ °C},$ common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	10	٨		
I _{RMS}		16	A		
V _{DRM} /V _{RRM}	Range ⁽¹⁾	800, 1200	V		
I _{TSM}		200	А		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ	Range	-40 to +125	°C		

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 ℃ mA
VS-16TTS08-M3	800	800	10
VS-16TTS12-M3	1200	1200	10



FREE





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				VALUES		T
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 98 °C, 180° conduction, half sine wave		10		
Maximum RMS on-state current	I _{RMS}			16		
Maximum peak, one-cycle,		10 ms sine p	ulse, rated V _{RRM} applied	11	70	A
non-repetitive surge current	I _{TSM}	10 ms sine pi	ulse, no voltage reapplied	20	00	
Maximum I ² t for fusing	l ² t	10 ms sine p	ulse, rated V _{RRM} applied	144		A ² s
	141	10 ms sine pulse, no voltage reapplied		200		A-S
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied		20	00	A²√s
Maximum on-state voltage drop	V _{TM}	10 A, T _J = 25 °C		1	.4	V
On-state slope resistance	r _t	T 405.00		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.1	V
	1 /1	T _J = 25 °C		0.5		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	1	0	
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A 16TTS08PbF, 16TTS12PbF, T_J = 25 °C		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		20	00	1
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$		50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			15	50	A∕µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+ I _{GM}		1.5	А
Maximum peak negative gate voltage	- V _{GM}		10	V
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	90	mA
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T_J = 25 °C	60	
		Anode supply = 6 V, resistive load, T_J = 125 °C	35	
	V _{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	3.0	
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	V
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v
Maximum DC gate voltage not to trigger	V _{GD}	$T = 125 \circ C M$ = Poted value	0.25	
Maximum DC gate current not to trigger	I _{GD}	$T_{\rm J} = 125 \text{ °C}, V_{\rm DRM} = \text{Rated value} $ 2.0		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T 105 %Q	4	μs
Typical turn-off time	tq	- T _J = 125 °C	110	

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.3		
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf ⋅ cm	
	maximum			12 (10)	(lbf ⋅ in)	
			Coop of the TO 220AB 21	16TT	rso8	
Marking device			Case style TO-220AB 3L		16TTS12	

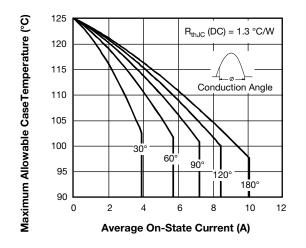
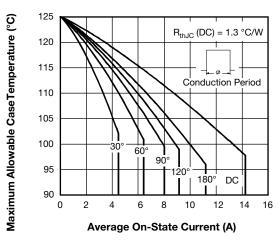


Fig. 1 - Current Rating Characteristics







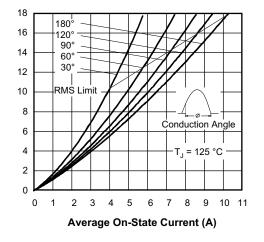
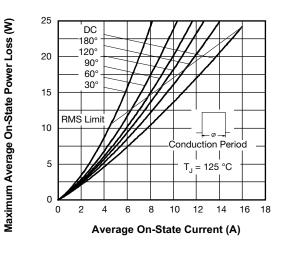
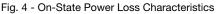


Fig. 3 - On-State Power Loss Characteristics





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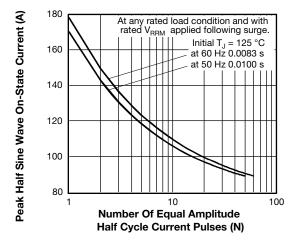


Fig. 5 - Maximum Non-Repetitive Surge Current

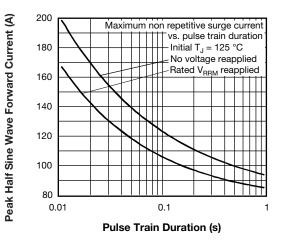


Fig. 6 - Maximum Non-Repetitive Surge Current

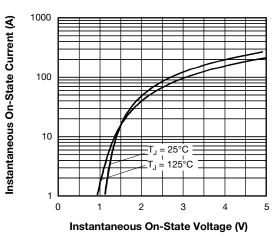


Fig. 7 - On-State Voltage Drop Characteristics

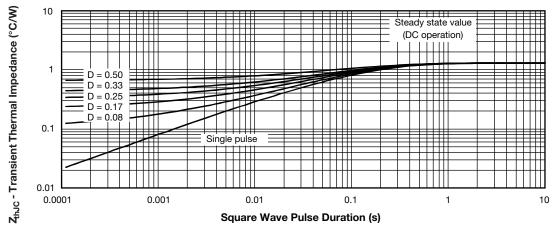
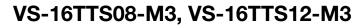


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



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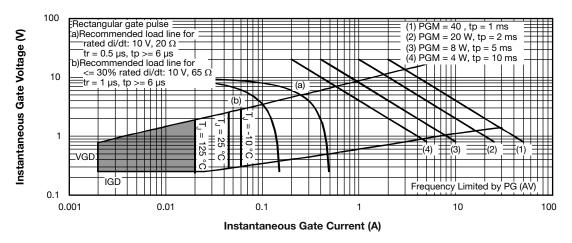


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

www.vishay.com

ORDERING INFORMATION (Example)				
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION		
VS-16TTS08-M3	50	Antistatic plastic tubes		
VS-16TTS12-M3	50	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS		
Dimensions	www.vishay.com/doc?96154	
Part marking information	www.vishay.com/doc?95028	

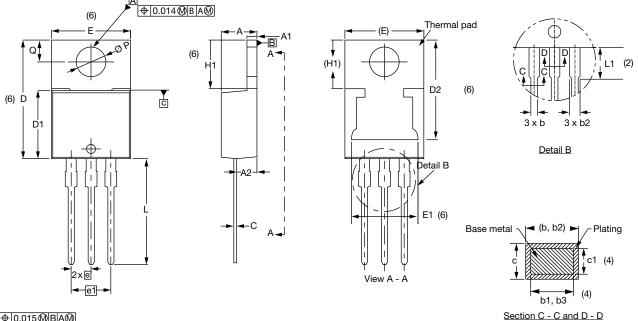
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TO-220AB 3L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

MILLIMETERS	INCHES

Conforms to JEDEC[®] outline TO-220AB

SYMBOL			INTOLIEO		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1

⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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